SMD Schottky Barrier Diode

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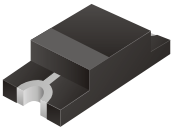
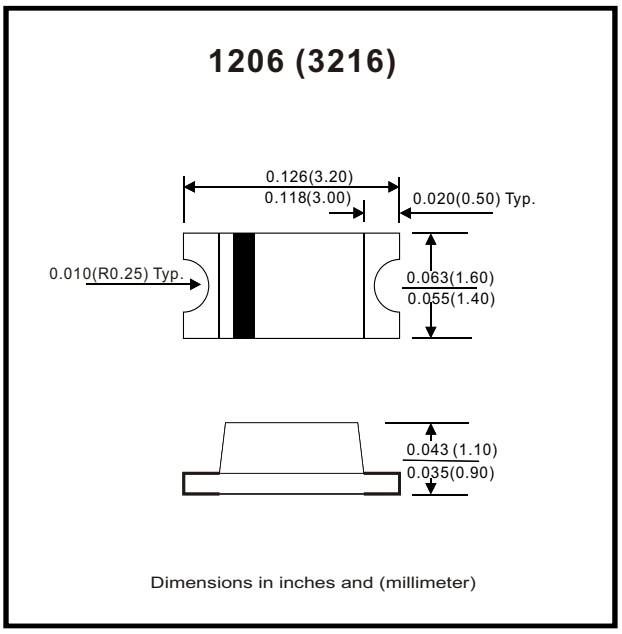
CDBN00340

Io = 30mA
V_R = 40 Volts



Features

- Designed for mounting on small surface
- Extremely thin package
- Low stored charge
- Majority carrier conduction



Mechanical data

Case: 12063(3216)Standard package, molded plastic.

Terminals: Solder plated, solderable per MIL-STD-750, method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any.

Weight: 0.0085 gram. (approximately)

Maximum Rating (at T_A = 25℃ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V_{RRM}			45	V
Reverse voltage		V_R			40	V
Average forward current		Io			30	mA
Forward current, surge peak	8.3 ms single half sine-wave superimposed on rate load (JEDEC method)	I_{FSM}		500		mA
Power Dissipation		P_D			200	mW
Storage temperature		T_{STG}	-40		+125	℃
Junction temperature		Tj	-40		+125	℃

Electrical Characteristics (at T_A = 25℃ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 1 mA DC	V_F			0.37	V
Reverse current	V_R = 40 V	I_R			1.00	uA
Reverse current	V_R = 30 V	I_R			0.50	uA
Capacitance between terminals	f = 1MHz, and 1 VDC reverse voltage	C_T		2		pF

RATING AND CHARACTERISTIC CURVES (CDBN00340)

Fig. 1 - Forward characteristics

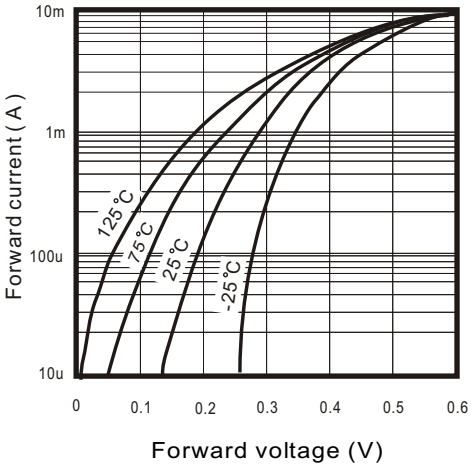


Fig. 1 - Forward characteristics

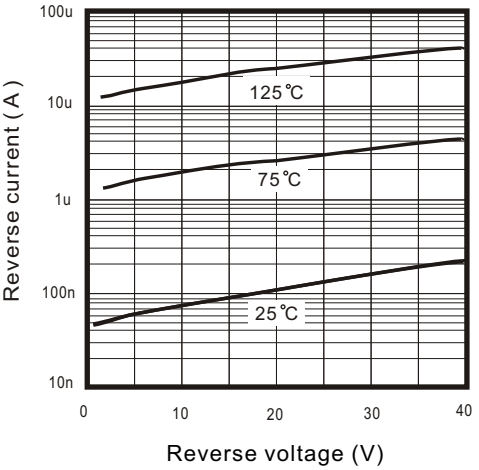


Fig. 3 - Capacitance between terminals characteristics

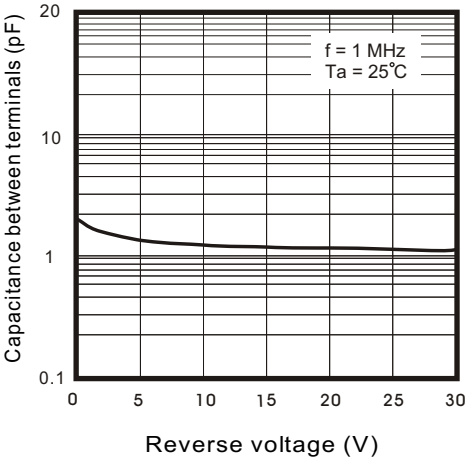


Fig. 4 - Derating curve